

EE320 - Lab #9

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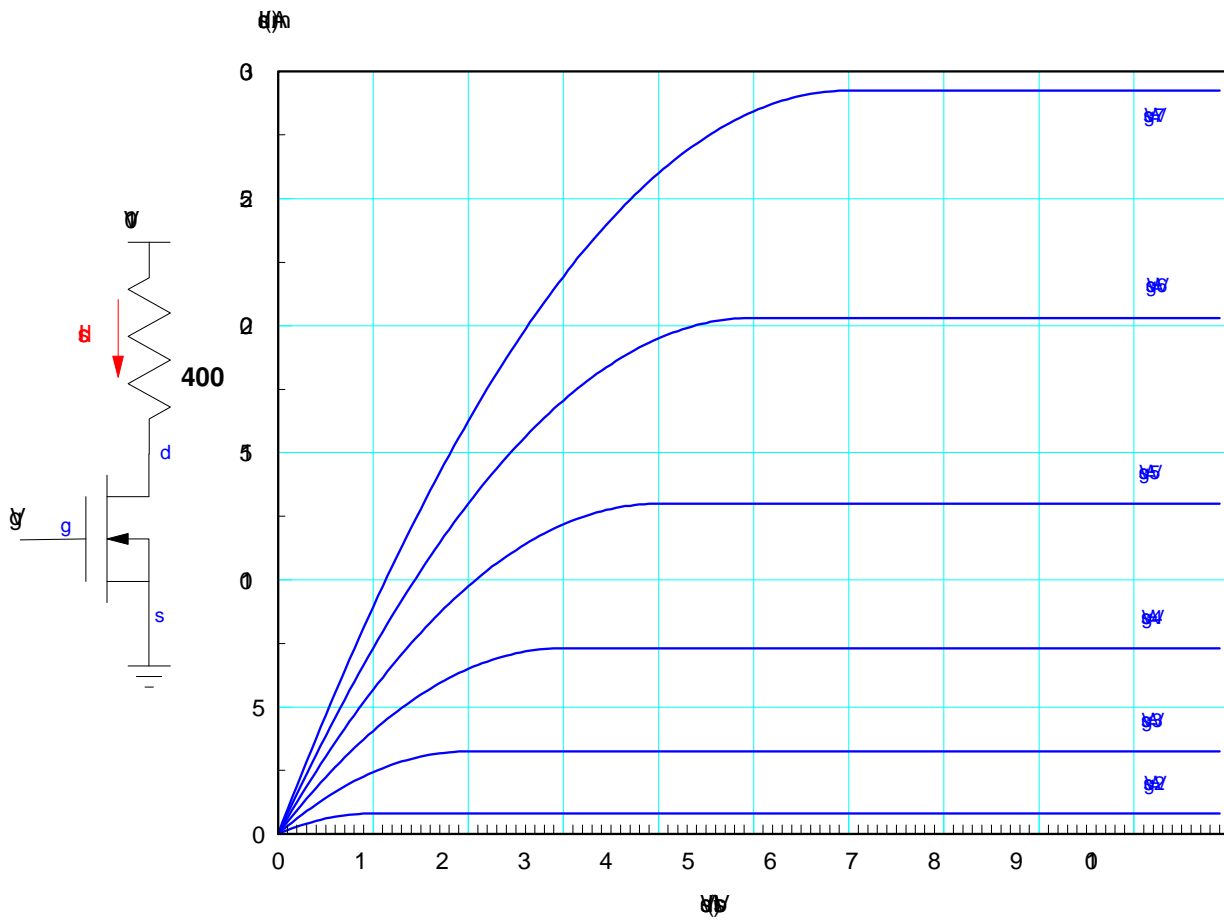
MOS

1) The VI characteristics for an n-channel MOSFET are shown below.

- Label the off / ohmic / and saturated regions
- Determine the transconductance gain, k_n . Assume $V_{th} = 1.00V$

2) Draw the load-line for the circuit below. From the load line, determine the Q-point (V_{ds} , I_{ds}) when

- $V_g = 0V$
- $V_g = 4V$
- $V_g = 7V$



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The characteristics for a IRF3710 MOSFET are

- Max Current = 57A continuous (180A pulsed)
- $R_{ds} = 0.023 \text{ Ohms @ } 6V_{gs} = 10V @ I_d = 28A$
- $2V < V_{th} < 4V$

3) Determine the transconductance gain, k_n

4) The CircuitLab model for an IRF3710 MOSFET is

- $k = 48.1147 \frac{A}{V^2}$
- $V_{th} = 3.39715V$

Using the CircuitLab parameters, determine the voltages for the following circuit for

- $V_{in} = V_g = 0V$
- $V_{in} = V_g = 5V$
- $V_{in} = V_g = 10V$